

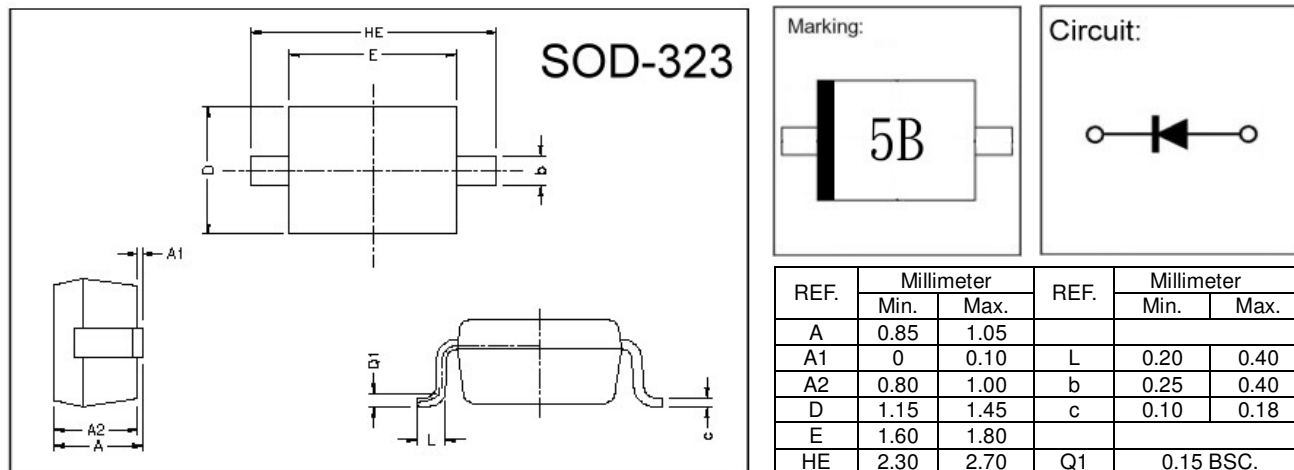
GD501SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 45V, CURRENT 0.1A

Description

The GD501SD is designed for low power rectification and high reliability.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	45	V
Maximum RMS Voltage	V _{RMS}	32	V
Maximum DC Blocking Voltage	V _{DC}	40	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	1.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	6.0	pF
Maximum Average Forward Rectified Current	I _o	0.1	A
Total Power Dissipation	PD	225	mW

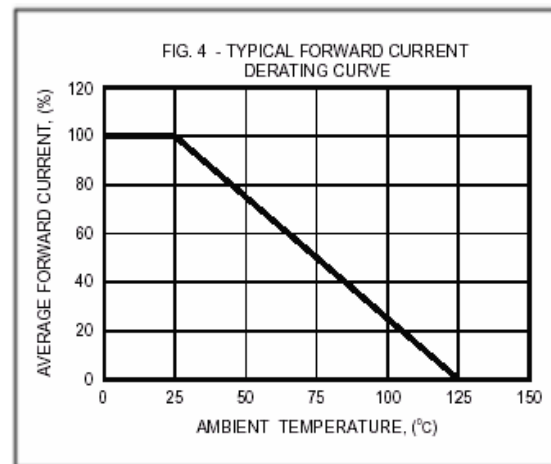
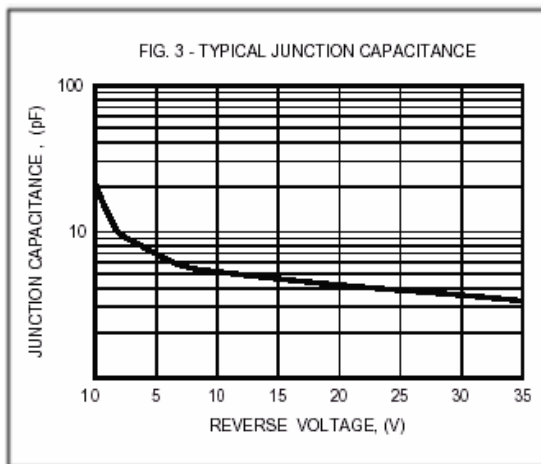
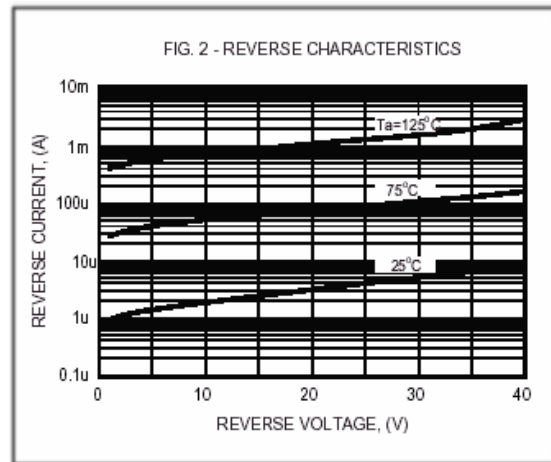
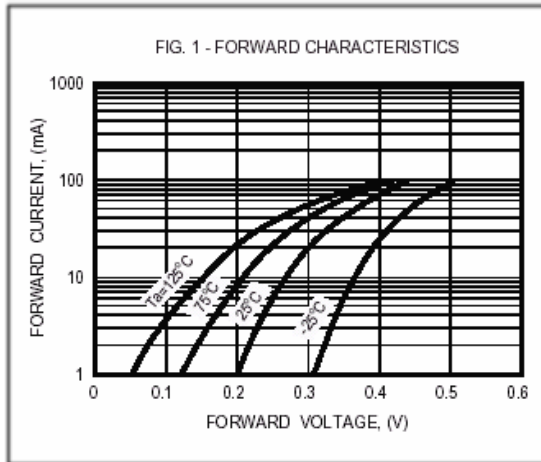
Characteristics at Ta = 25°C

Characteristics	Symbol	Max	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _{F(1)}	0.55	V	I _F = 100mA
Maximum Instantaneous Forward Voltage	V _{F(2)}	0.34	V	I _F = 10 mA
Maximum Average Reverse Current	I _R	30.0	uA	V _R = 10V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 10.0 volt.

2. ESD sensitive product handling required.

Characteristics Curve



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